

General Purpose Transistor

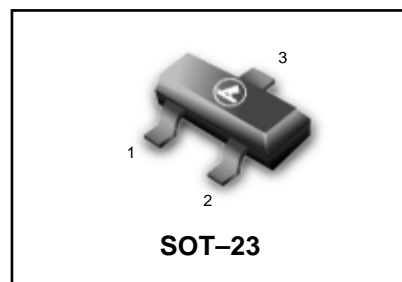
DESCRIPTION

L2SA1365*LT1G is a mini package silicon PNP epitaxial transistor, designed with high collector current and small VCE(sat).

FEATURE

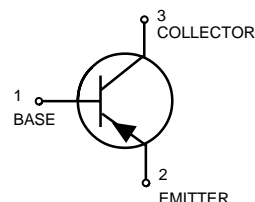
- Small collector to emitter saturation voltage.
VCE(sat)=-0.2V typ
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting
- High collector current I_{CM}=-1A
- High gain band width product f_T=180MHz typ
- We declare that the material of product compliance with RoHS requirements.
- We declare that the material of product is ROHS compliant
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements, AEC-Q101 Qualified and PPAP Capable.

L2SA1365*LT1G
S-L2SA1365*LT1G



APPLICATION

Small type motor drive, relay drive, power supply.



MAXIMUM RATINGS (T_a=25°C)

Symbol	Parameter	Ratings	Unit
V _{CBO}	Collector to Base voltage	-25	V
V _{CEO}	Collector to Emitter voltage	-20	V
V _{EBO}	Emitter to Base voltage	-4	V
I _O	Collector current	-700	mA
P _c	Collector dissipation	150	mW
T _j	Junction temperature	+125	°C
T _{stg}	Storage temperature	-55~+125	°C

ORDERING INFORMATION

Device	Marking	Shipping
L2SA1365ELT1G S-L2SA1365ELT1G	AE	3000/Tape & Reel
L2SA1365ELT3G S-L2SA1365ELT3G	AE	10000/Tape & Reel
L2SA1365FLT1G S-L2SA1365FLT1G	AF	3000/Tape & Reel
L2SA1365FLT3G S-L2SA1365FLT3G	AF	10000/Tape & Reel
L2SA1365GLT1G S-L2SA1365GLT1G	AG	3000/Tape & Reel
L2SA1365GLT3G S-L2SA1365GLT3G	AG	10000/Tape & Reel

ELECTRICAL CHARACTERISTICS (T_a=25°C)

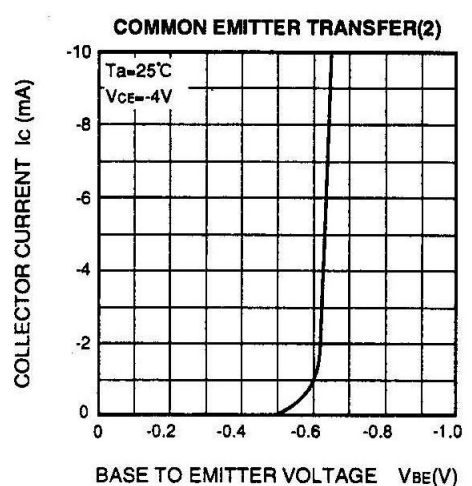
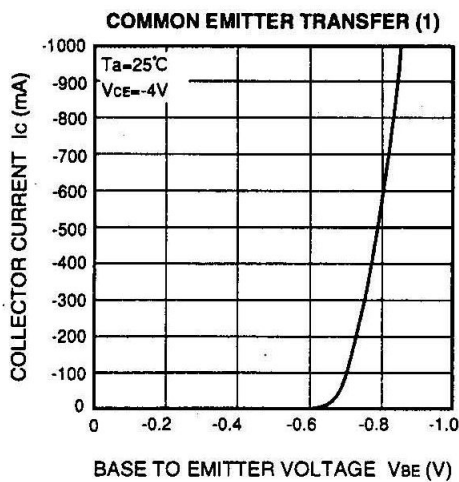
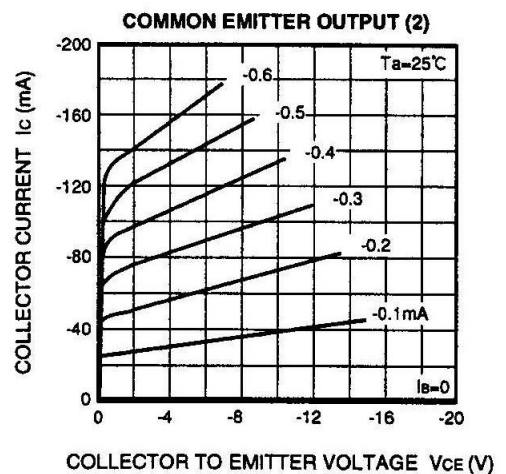
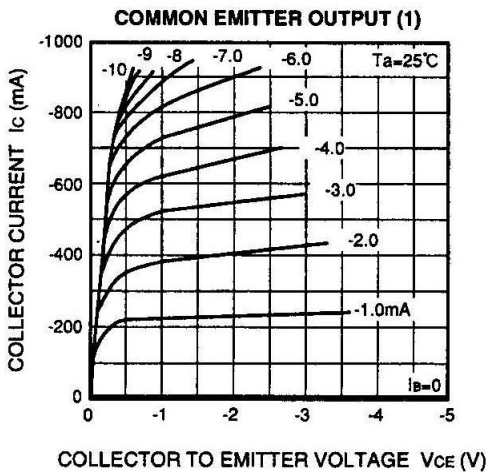
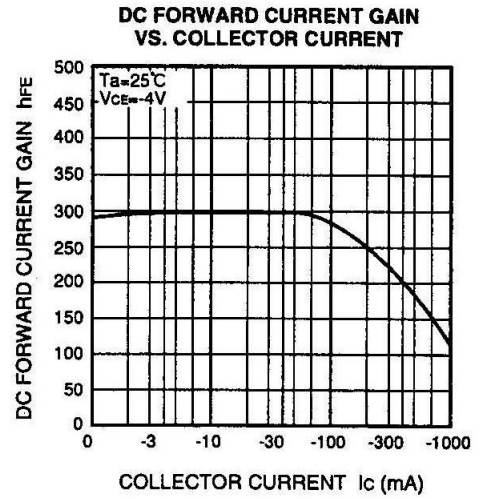
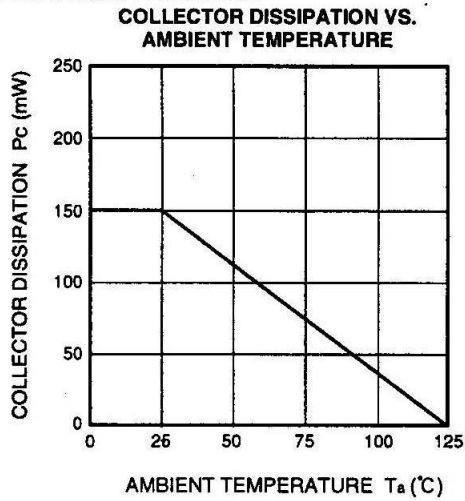
Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to B break down voltage	V(BR) _{CBO}	I _C =-10 μA, I _E =0	-25	-	-	V
E to B break down voltage	V(BR) _{EBO}	I _E =-10 μA, I _C =0	-4	-	-	V
C to E break down voltage	V(BR) _{CEO}	I _C =-100 μA, R _{BE} =∞	-20	-	-	V
Collector cut off current	I _{CBO}	V _{CB} =-25V, I _E =0mA	-	-	-1	μA
Emitter cut off current	I _{EBO}	V _{EB} =-2V, I _C =0mA	-	-	-1	μA
DC forward current gain	hFE	V _{CE} =-4V, I _C =-100mA ※	150	-	800	
C to E Saturation Voltage	VCE(sat)	I _C =-500mA, I _B =-25mA	-	-0.2	-0.5	V
Gain bandwidth product	f _T	V _{CE} =-6V, I _E =10mA	-	180	-	MHz

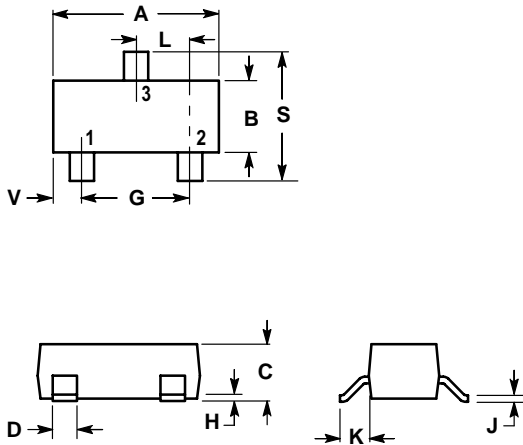
※) It shows hFE classification in below table.

Item	E	F	G
hFE Item	150~300	250~500	400~800

L2SA1365*LT1G
S-L2SA1365*LT1G

TYPICAL CHARACTERISTICS



SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

